

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

Complementary Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves
- Straight Lead Version in Plastic Sleeves ("1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series
- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings:
 - ♦ Human Body Model, 3B > 8000 V
 - ♦ Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Packages*



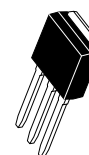
ON Semiconductor®

<http://onsemi.com>

**SILICON
POWER TRANSISTORS
3 AMPERES
40 AND 100 VOLTS
15 WATTS**

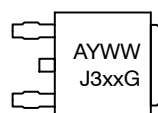


**DPAK
CASE 369C
STYLE 1**

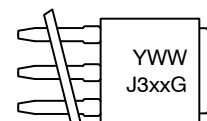


**DPAK-3
CASE 369D
STYLE 1**

MARKING DIAGRAMS



DPAK



DPAK-3

A	= Site Code
Y	= Year
WW	= Work Week
xx	= 1, 1C, 2, or 2C
G	= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	V_{CEO}	40 100	Vdc
Collector–Base Voltage MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	V_{CB}	40 100	Vdc
Emitter–Base Voltage	V_{EB}	5	Vdc
Collector Current Continuous Peak	I_C	3 5	Adc
Base Current	I_B	1	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.56 0.012	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	8.3	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Ambient*	$R_{\theta JA}$	80	$^\circ\text{C}/\text{W}$
Lead Temperature for Soldering Purposes	T_L	260	$^\circ\text{C}$

*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 30\text{ mAdc}$, $I_B = 0$) MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	$V_{CE(sus)}$	40 100	– –	Vdc
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	I_{CEO}	– –	50 50	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{EB} = 0$)	I_{CES}	–	20	μAdc
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	1	mAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 1\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$) ($I_C = 3\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$)	h_{FE}	25 10	– 50	
Collector–Emitter Saturation Voltage ($I_C = 3\text{ Adc}$, $I_B = 375\text{ mAdc}$)	$V_{CE(sat)}$	–	1.2	Vdc
Base–Emitter On Voltage ($I_C = 3\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$)	$V_{BE(on)}$	–	1.8	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product (Note 2) ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1\text{ MHz}$)	f_T	3	–	MHz
Small–Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ kHz}$)	h_{fe}	20	–	

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS

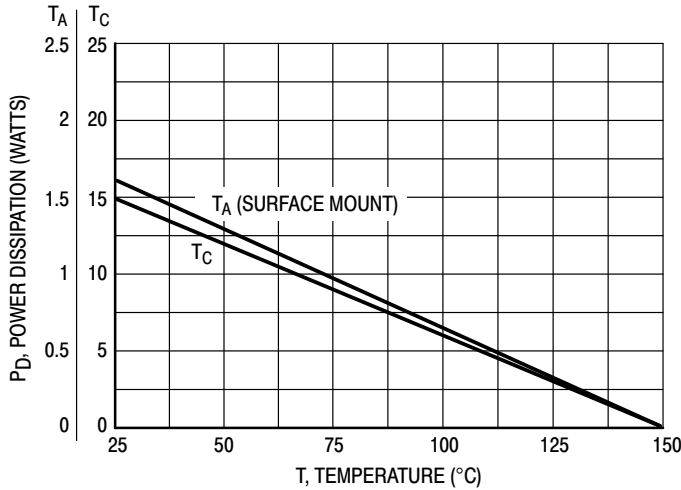
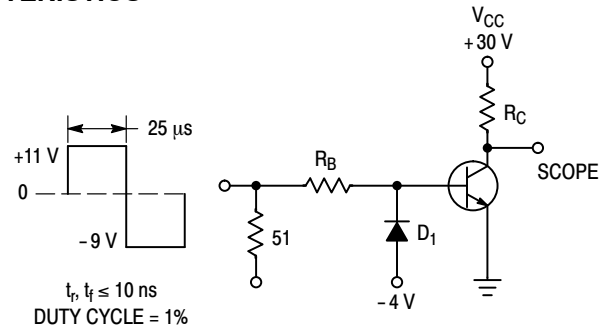


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
 D_1 MUST BE FAST RECOVERY TYPE, e.g.:
 1N5825 USED ABOVE $I_B \approx 100$ mA
 MSD6100 USED BELOW $I_B \approx 100$ mA
 REVERSE ALL POLARITIES FOR PNP.

Figure 2. Switching Time Test Circuit

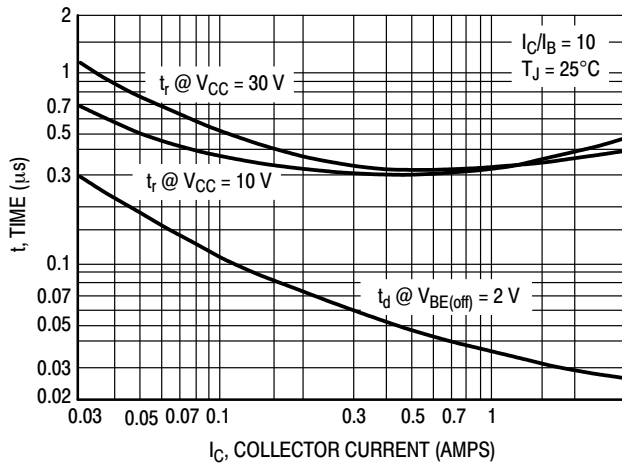


Figure 3. Turn-On Time

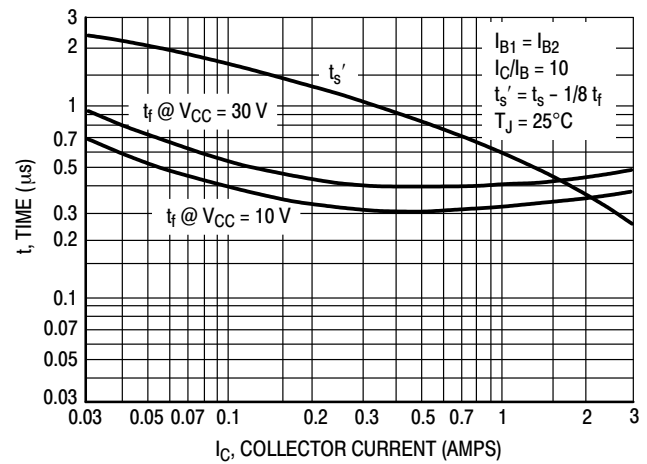


Figure 4. Turn-Off Time

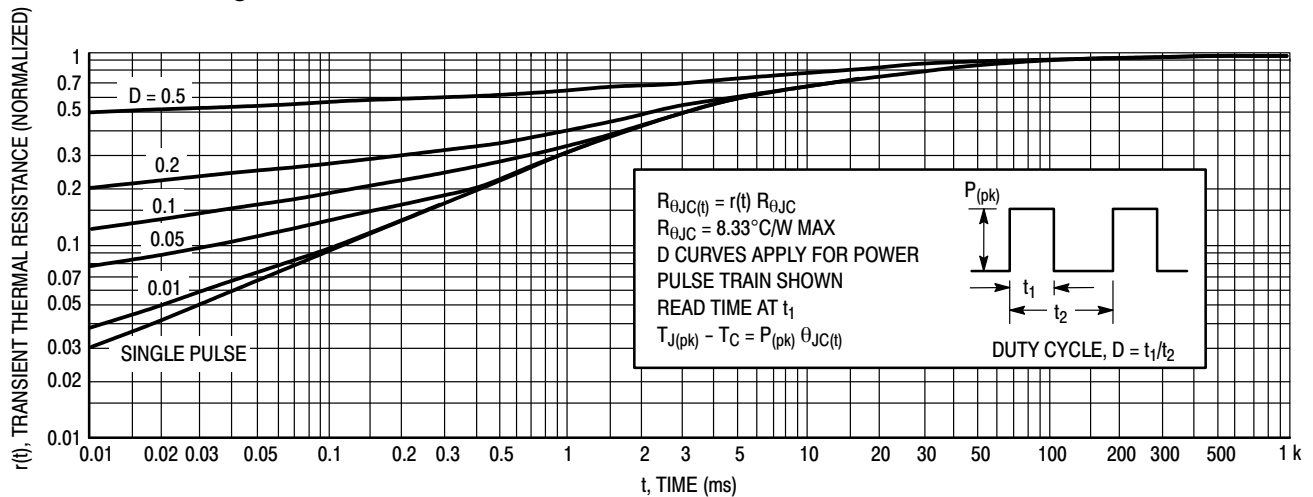


Figure 5. Thermal Response

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)

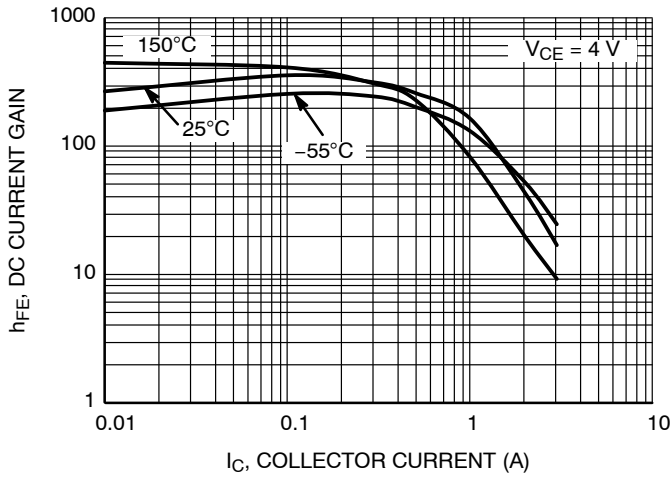


Figure 6. DC Current Gain at $V_{CE} = 4\text{ V}$

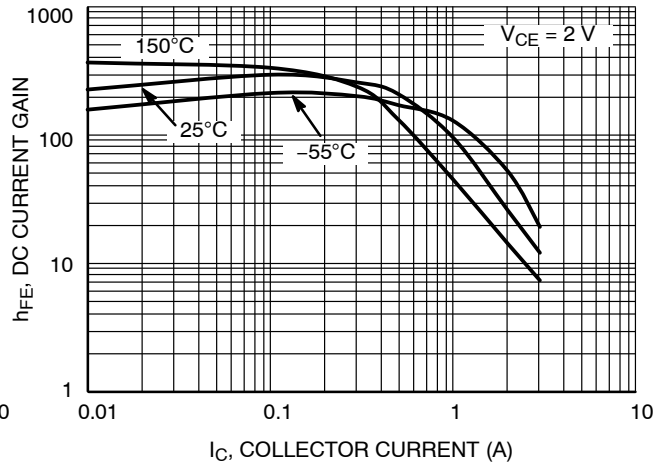


Figure 7. DC Current Gain at $V_{CE} = 2\text{ V}$

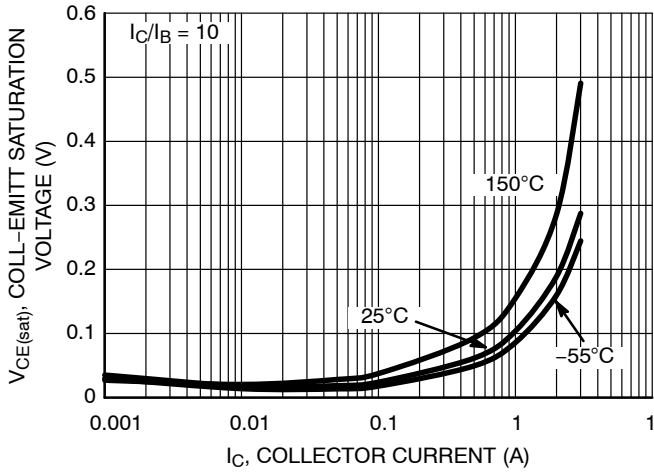


Figure 8. Collector-Emitter Saturation Voltage

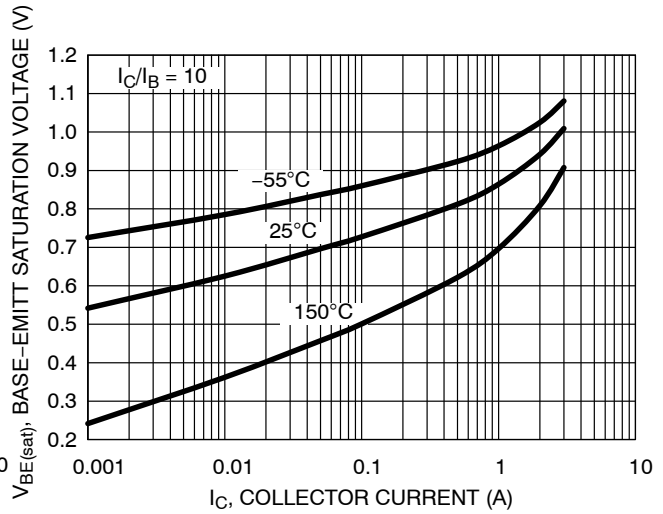


Figure 9. Base-Emitter Saturation Voltage

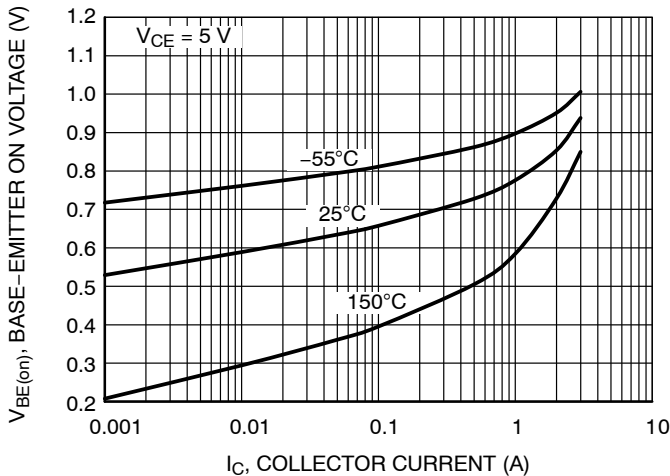


Figure 10. Base-Emitter "On" Voltage

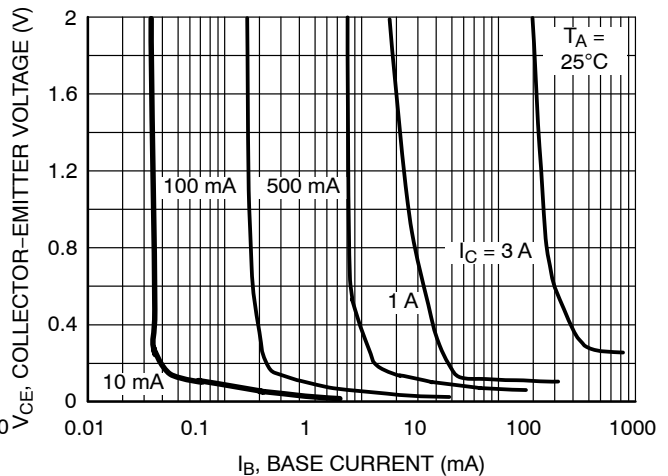


Figure 11. Collector Saturation Region

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)

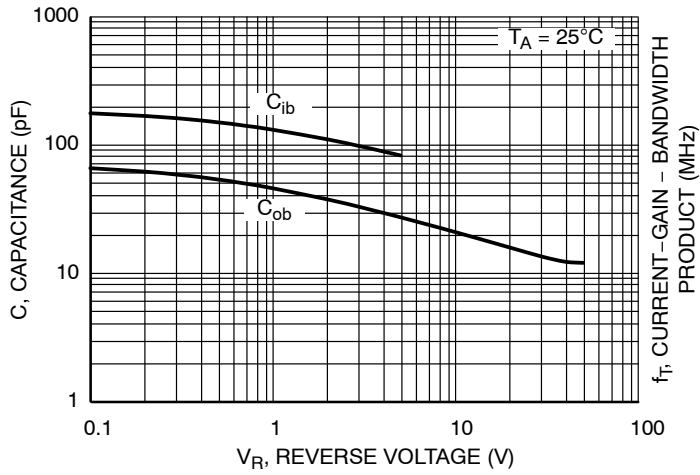


Figure 12. Capacitance

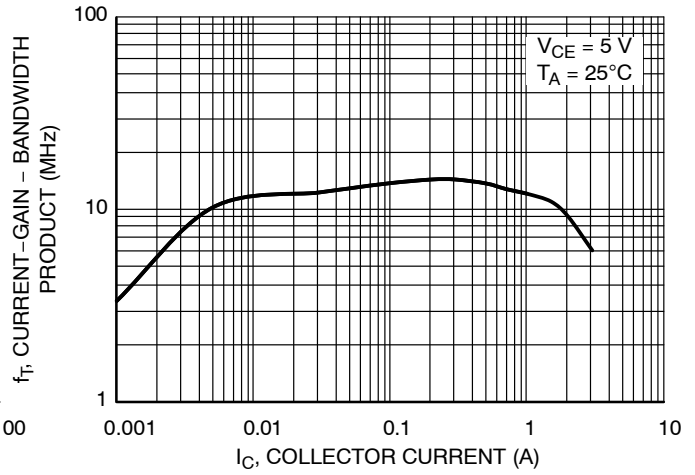


Figure 13. Current-Gain-Bandwidth Product

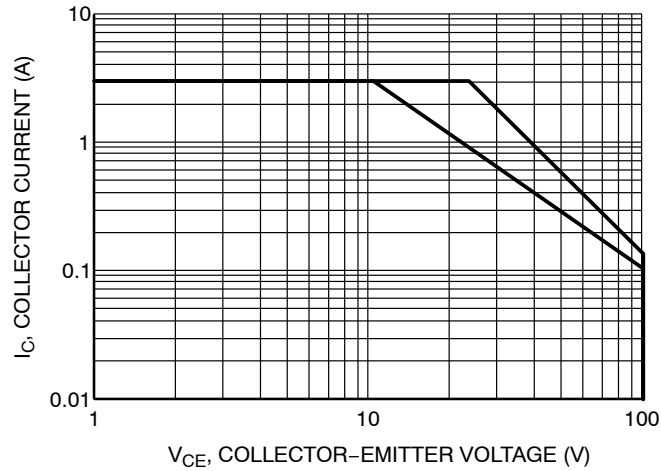


Figure 14. Safe Operating Area

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS – MJD32, MJD32C (PNP)

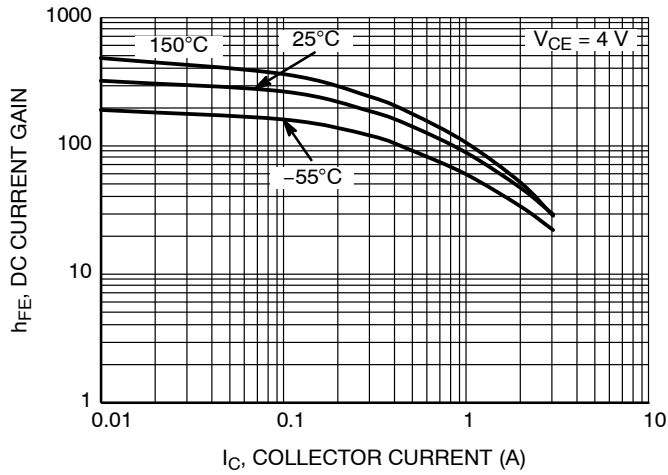


Figure 15. DC Current Gain at $V_{CE} = 4\text{ V}$

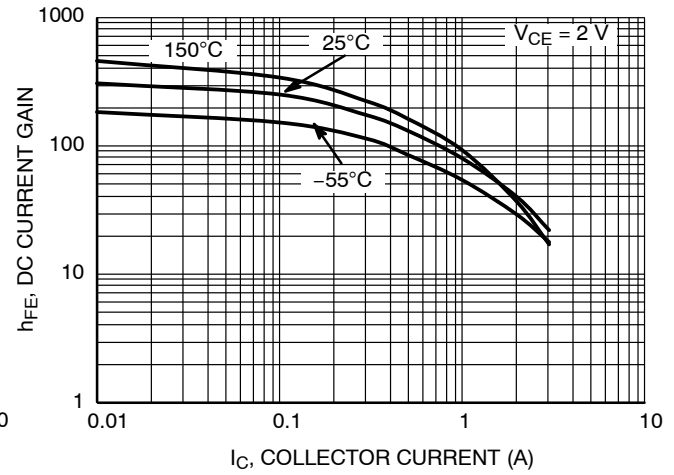


Figure 16. DC Current Gain at $V_{CE} = 2\text{ V}$

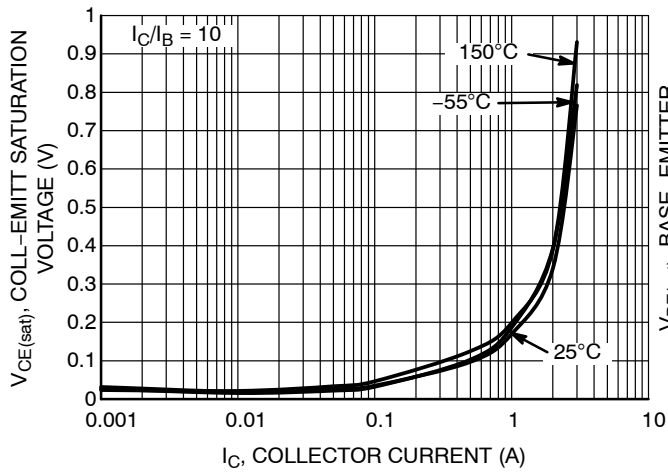


Figure 17. Collector-Emitter Saturation Voltage

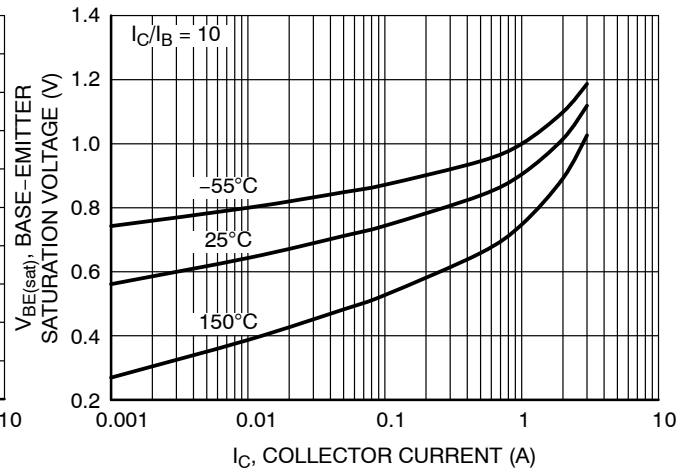


Figure 18. Base-Emitter Saturation Voltage

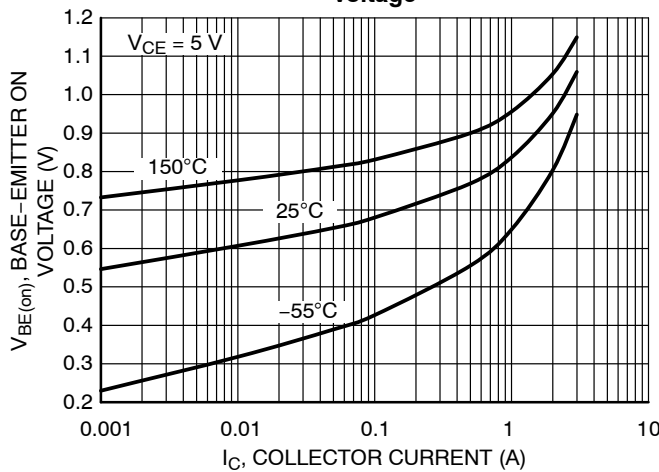


Figure 19. Base-Emitter "On" Voltage

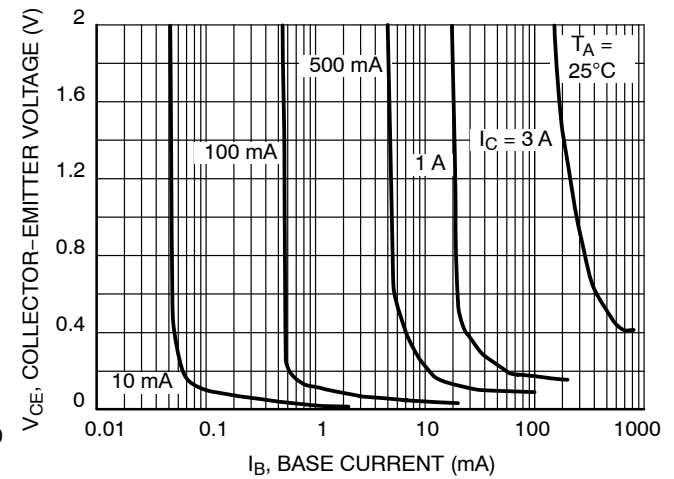


Figure 20. Collector Saturation Region

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

TYPICAL CHARACTERISTICS

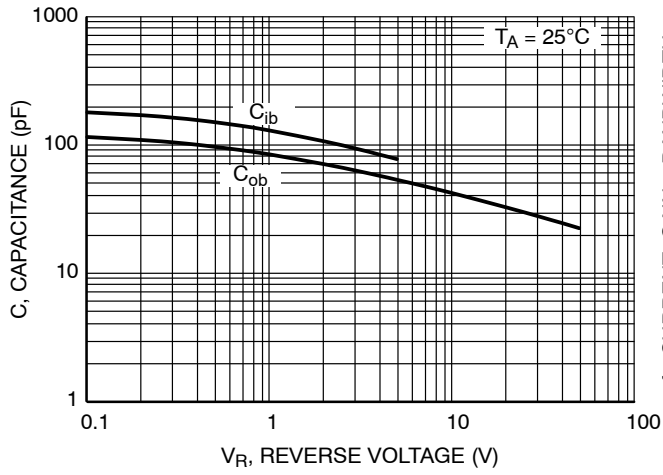


Figure 21. Capacitance

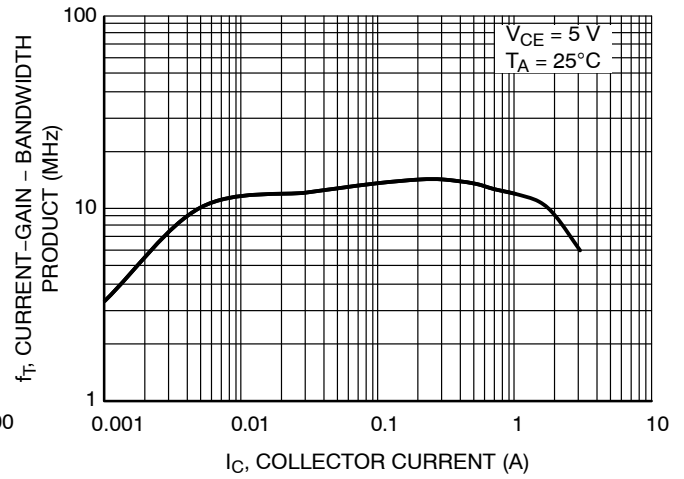


Figure 22. Current-Gain-Bandwidth Product

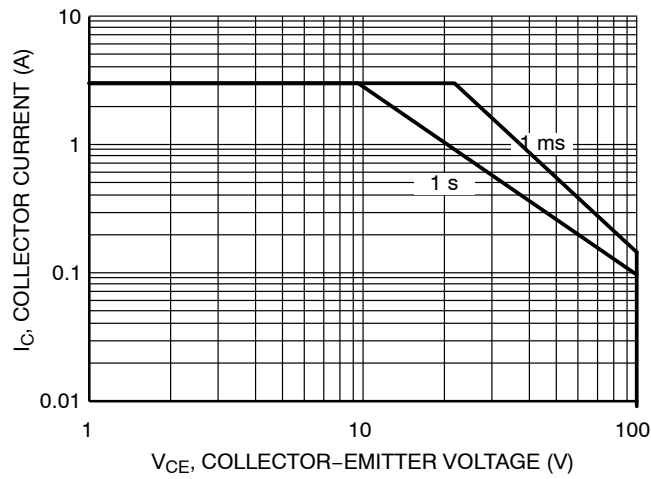


Figure 23. Safe Operating Area

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

ORDERING INFORMATION

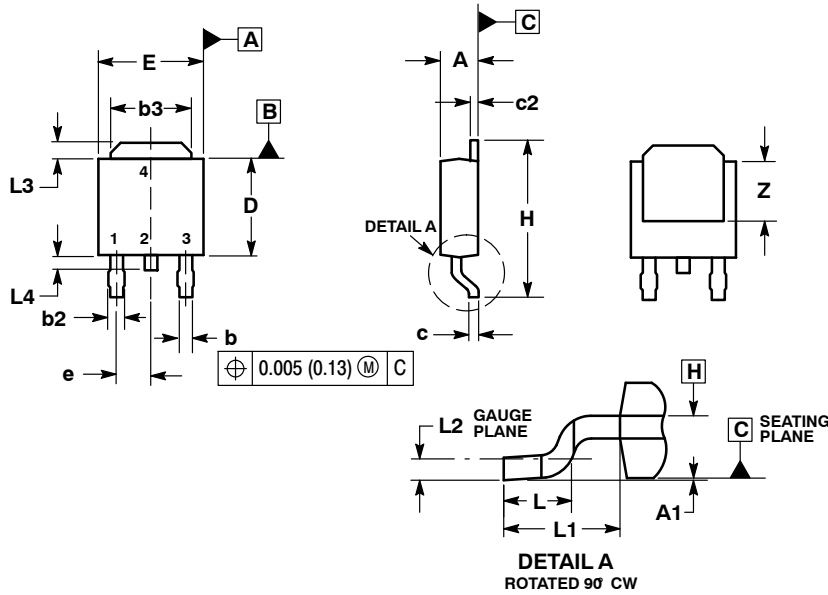
Device	Package Type	Package	Shipping [†]
MJD31CG	DPAK (Pb-Free)	369C	75 Units / Rail
MJD31C1G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MJD31CRLG	DPAK (Pb-Free)	369C	1,800 Tape & Reel
MJD31CT4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
NJVMJD31CT4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
MJD31T4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
NJVMJD31T4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
MJD32CG	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD32CG	DPAK (Pb-Free)	369C	75 Units / Rail
MJD32CRLG	DPAK (Pb-Free)	369C	1,800 Tape & Reel
MJD32CT4	DPAK	369C	2,500 Tape & Reel
MJD32CT4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
NJVMJD32CT4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
MJD32RLG	DPAK (Pb-Free)	369C	1,800 Tape & Reel
MJD32T4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel
NJVMJD32T4G	DPAK (Pb-Free)	369C	2,500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE D

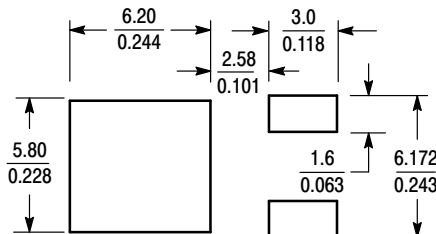


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

STYLE 1:

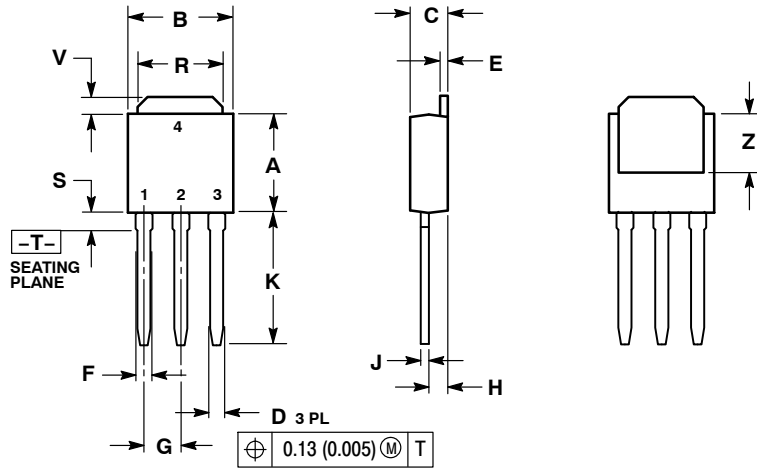
- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

PACKAGE DIMENSIONS

IPAK CASE 369D-01 ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:

- PIN 1: BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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Sales Representative



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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